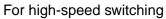
Unit: mm

# 2SA1495

## Silicon PNP epitaxial planar type



#### Featu

- High fo
- High-s •
- High c
- I type • the prin

						Unit: mm
For high-speed switc	hing			1	7.0±0.3 3.0±0.2	3.5±0.2
5 1	5					
				7.2±0.3		
Features				2.7		
• High foward current transfer ratio h <sub>FE</sub>					1.1±0.1	→ 0.85±0.1
• High-speed switching					► <b>0.75±0.1</b>	<u>→ 0.4±0.1</u>
• High collector to base voltage V <sub>CBO</sub>						
• I type package enabling direct soldering of the radiating fin to					↓ ↓ ↓ <u>2.3±0.2</u>	U
the printed circuit board, etc. of small electronic equipment.					4.6±0.4	
					1 2 3	1:Base
Absolute Maximur	n Ratings	$(T - 25^{\circ}C)$				2:Collector 3:Emitter
		$(1_{C}-25C)$				I Type Package
Parameter	Symbol	Ratings	Unit			Unit: mm
Collector to base voltage	V <sub>CBO</sub>	-400	V		7.0±0.3 2.0±0.2	3:5±0.2 0 to 0.15
Collector to emitter voltage	V <sub>CEO</sub>	-400	V			
Emitter to base voltage	V <sub>EBO</sub>	-7	V		3.0±0.2	EE0.2
Peak collector current	I <sub>CP</sub>	-1.2	Α	10.2±0.3	and the second se	
Collector current	Ic	- 0.6	А			
Collector power $T_C = 25^{\circ}C$	D	15	W		0.75±0.1	0.5 max.
dissipation Ta=25°C	PC	1.3	W		±0.1_  +	0 to 0.15
Junction temperature	Tj	150	°C	LOV F		1:Base
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	A A	2.3±0.2	2:Collector
			2	100	4.6±0.4	3:Emitter I Type Package (Y)
Electrical Charact	eristics (T	-25°C)				) po 1 uonugo (1)
		-25 ()	``	K.		

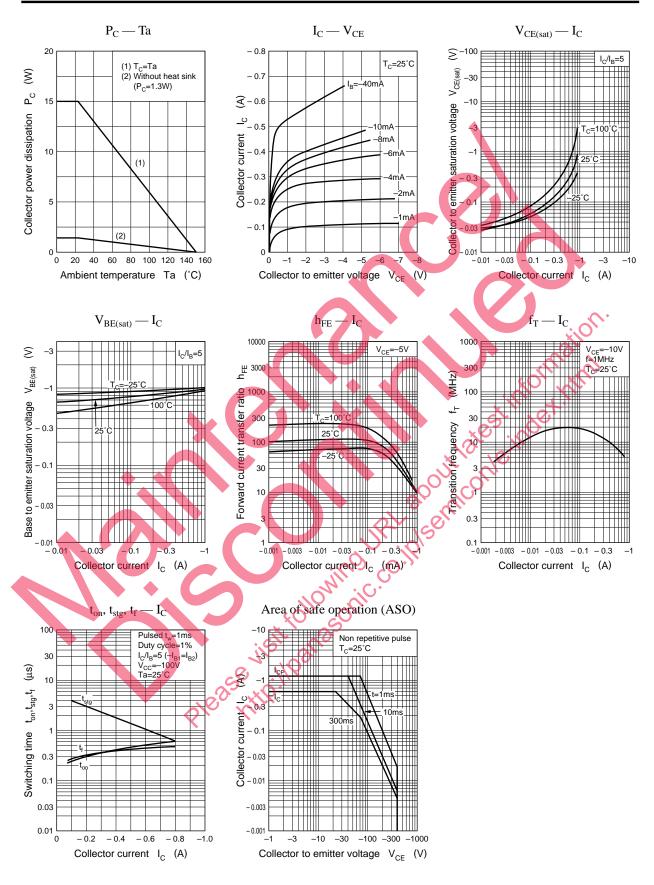
#### Abso

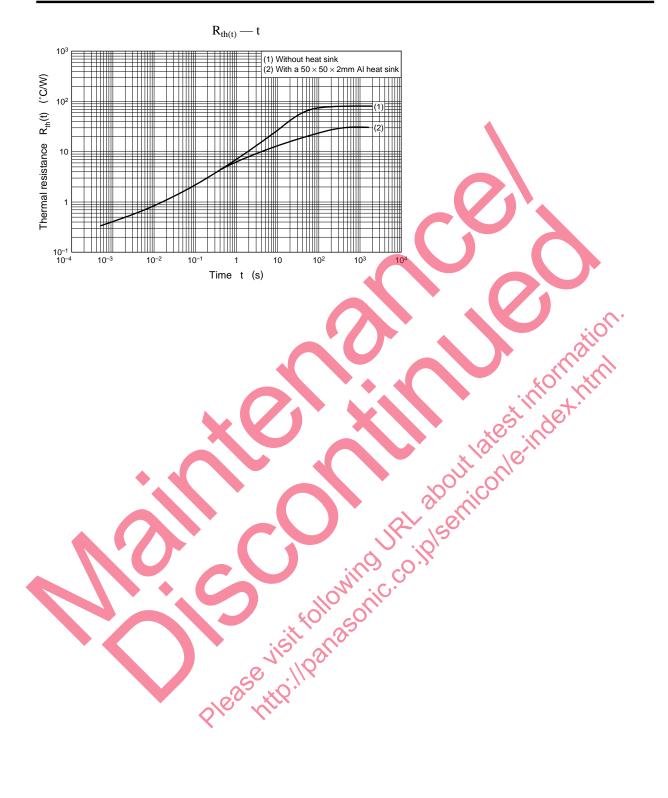
### Electrical Characteristics (T<sub>c</sub>=25°C)

Paramotor	Symbol	Conditions	min	tun	may	Unit
Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I <sub>CBO</sub>	$V_{CB} = -400V, I_E = 0.4$			-100	μΑ
Emitter cutoff current	I <sub>EBO</sub>	$V_{\rm HB} = -7V, I_{\rm C} = 0$			-100	μΑ
Collector to emitter voltage	V <sub>CEO</sub>	$I_{\rm C} = -10 {\rm mA}, I_{\rm B} = 0$	-400			V
Forward current transfer ratio	h <sub>FE1</sub> *	$V_{CE} = -5V, I_C = -100mA$	30		160	
	h <sub>FE2</sub>	$V_{CE} = -5V, I_{C} = -300mA$	10			
Collector to emitter saturation voltage	V <sub>CE(sat)</sub>	$Q_{\rm C} = -300 {\rm mA}, I_{\rm B} = -60 {\rm mA}$			-1.0	V
Base to emitter saturation voltage	V <sub>BE(sat)</sub>	$I_{\rm C} = -300 {\rm mA}, I_{\rm B} = -60 {\rm mA}$			-1.5	V
Transition frequency	f <sub>T</sub>	$V_{CE} = -10V$ , $I_C = -100mA$ , $f = 1MHz$		15		MHz
Turn-on time	t <sub>on</sub>	$I_{\rm C} = -300 {\rm mA},$			1.0	μs
Storage time	t <sub>stg</sub>	$I_{B1} = -60 \text{mA}, I_{B2} = 60 \text{mA},$			3.5	μs
Fall time	t <sub>f</sub>	$V_{CC} = -100V$			1.0	μs

#### \*hFE1 Rank classification

Rank	Q	Р	0
h <sub>FE1</sub>	30 to 60	50 to 100	80 to 160





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